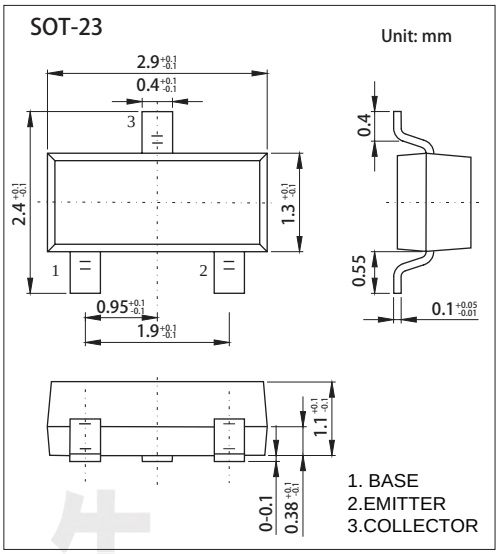
PNP Transistors

BC807



■ Features

- ● Ldeally suited for automatic insertion
- ● Epitaxial planar die construction
- ● Complementary to BC817

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	417	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CBO}	I_C= -10 μA， I_E=0	-50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA， I_B=0	-45			
Emitter - base breakdown voltage	V_{EBO}	I_E= -10 μA， I_C=0	-5			
Collector cut-off current	I_{CBO}	V_{CB}= -45 V , I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B= -50mA			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B= -50mA			-1.2	
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	100		600	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -500mA	40			
Transition frequency	f_T	V_{CE}= -20 V,I_C= -10mA,f=100MHz	100			MHz

■ Classification of hFE(1)

Rank	BC807-16	BC807-16	BC807-16
Range	100-250	160-400	250-600
Marking	5A	5B	5C

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■ Typical Characterisitics